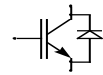


# Technische Information / Technical Information

IGBT-Module  
IGBT-Modules

## FZ 1200 R 17 KF6 B2

eupec



vorläufige Daten  
preliminary data

### Höchstzulässige Werte / Maximum rated values

#### Elektrische Eigenschaften / Electrical properties

Kollektor-Emitter-Sperrspannung collector-emitter voltage		$V_{CES}$	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	1200	A
	$T_C = 25^\circ\text{C}$	$I_C$	2400	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	$I_{CRM}$	2400	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$ , Transistor	$P_{tot}$	9,6	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/- 20V	V
Dauergleichstrom DC forward current		$I_F$	1200	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	$I_{FRM}$	2400	A
Grenzlastintegral der Diode $I^2t$ - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	$I^2t$	440	$\text{kA}^2\text{s}$
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	$V_{ISOL}$	4	kV

### Charakteristische Werte / Characteristic values

#### Transistor / Transistor

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 1200\text{A}, V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,7	3,2	V
	$I_C = 1200\text{A}, V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}$		-	3,2		V
Gate-Schwellenspannung gate threshold voltage	$I_C = 80\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$	$Q_G$	-	14,5	-	$\mu\text{C}$
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{ies}$	-	79	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{res}$	-	t.b.d.	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{CES}$	-	0,3	2,5	mA
	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}$		-	30		mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{GES}$	-	-	400	nA

prepared by: Oliver Schilling

date of publication: 12.11.1998

approved by: M. Hierholzer

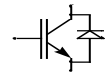
revision: 1

# Technische Information / Technical Information

IGBT-Module  
IGBT-Modules

## FZ 1200 R 17 KF6 B2

eupec



vorläufige Daten  
preliminary data

### Charakteristische Werte / Characteristic values

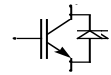
#### Transistor / Transistor

			min.	typ.	max.	
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 1200A, V_{CE} = 900V$	$t_{d,on}$	-	0,3	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 125^\circ C$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 1200A, V_{CE} = 900V$	$t_r$	-	0,16	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 125^\circ C$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 1200A, V_{CE} = 900V$	$t_{d,off}$	-	1,1	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 125^\circ C$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 1200A, V_{CE} = 900V$	$t_f$	-	0,13	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 1,2\Omega, T_{vj} = 125^\circ C$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 1200A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 1,2\Omega, T_{vj} = 125^\circ C, L_S = 50nH$	$E_{on}$	-	330	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 1200A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 1,2\Omega, T_{vj} = 125^\circ C, L_S = 50nH$	$E_{off}$	-	480	-	mWs
Kurzschlußverhalten SC Data	$t_p \leq 10\mu sec, V_{GE} \leq 15V$ $T_{vj} \leq 125^\circ C, V_{CC} = 1000V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$I_{SC}$	-	4800	-	A
Modulinduktivität stray inductance module		$L_{sCE}$	-	12	-	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	pro Zweig / per arm	$R_{CC+EE}$	-	0,08	-	m $\Omega$

### Charakteristische Werte / Characteristic values

#### Diode / Diode

			min.	typ.	max.	
Durchlaßspannung forward voltage	$I_F = 1200A, V_{GE} = 0V, T_{vj} = 25^\circ C$	$V_F$	-	2,2	2,6	V
	$I_F = 1200A, V_{GE} = 0V, T_{vj} = 125^\circ C$					
Rückstromspitze peak reverse recovery current	$I_F = 1200A, -di_F/dt = 7200A/\mu sec$	$I_{RM}$	-	700	-	A
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Sperrverzögerungsladung recovered charge	$I_F = 1200A, -di_F/dt = 7200A/\mu sec$	$Q_r$	-	160	-	$\mu As$
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Abschaltenergie pro Puls reverse recovery energy	$I_F = 1200A, -di_F/dt = 7200A/\mu sec$	$E_{rec}$	-	90	-	mWs
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					



**vorläufige Daten**  
**preliminary data**

**Thermische Eigenschaften / Thermal properties**

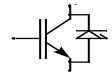
			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	$R_{thJC}$	-	-	0,013	K/W
	Diode/Diode, DC		-	-	0,025	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{Paste} = 1 \text{ W/m}^2\text{K} / \lambda_{grease} = 1 \text{ W/m}^2\text{K}$	$R_{thCK}$	-	0,008	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj}$	-	-	150	°C
Betriebstemperatur operation temperature		$T_{op}$	-40	-	125	°C
Lagertemperatur storage temperature		$T_{stg}$	-40	-	125	°C

**Mechanische Eigenschaften / Mechanical properties**

Gehäuse, siehe Anlage case, see appendix					
Innere Isolation internal insulation				AlN	
Kriechstrecke creepage distance				17	mm
Luftstrecke clearance				10	mm
CTI comperative tracking index				275	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M1		5	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	terminals M4	M2		2	Nm
	terminals M8			8 - 10	Nm
Gewicht weight		G		1050	g

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert.  
Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

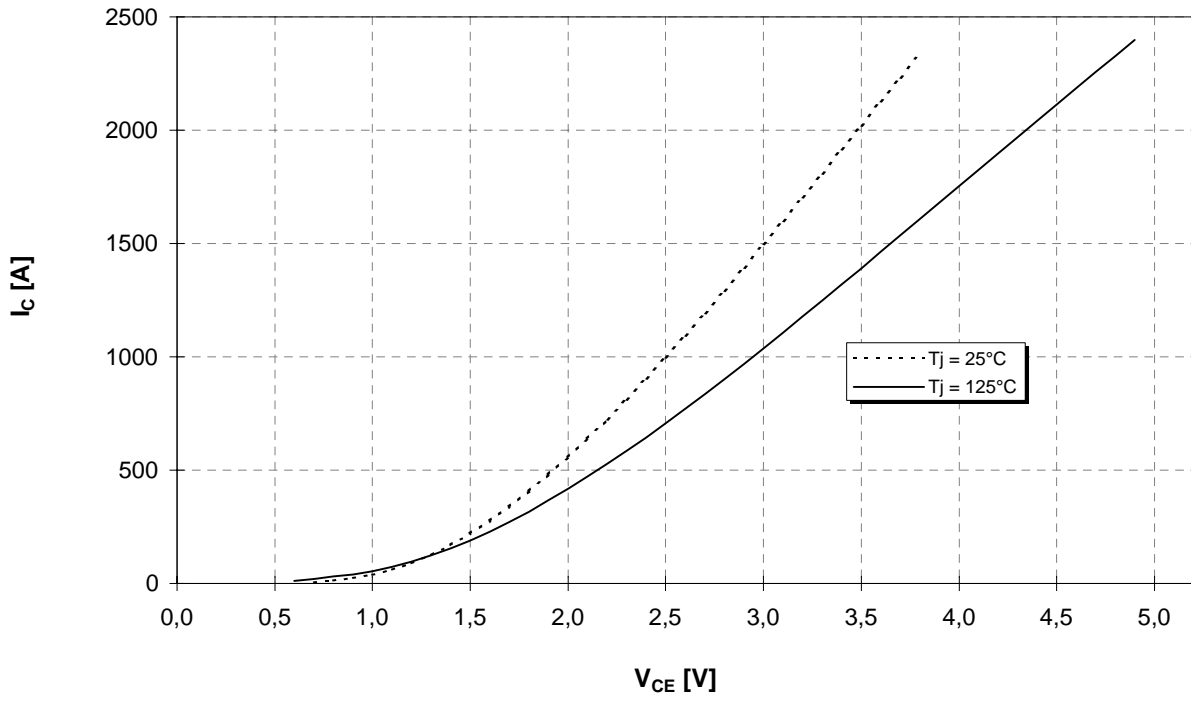
This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



**Ausgangskennlinie (typisch)**  
**Output characteristic (typical)**

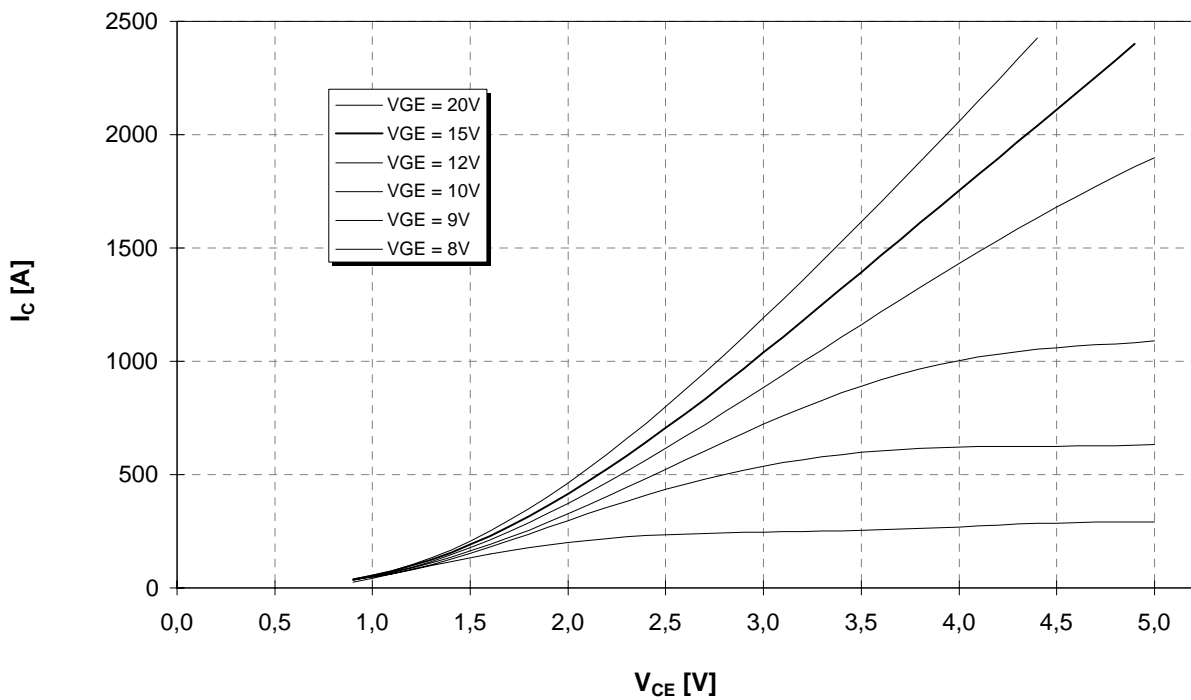
$I_c = f(V_{CE})$   
 $V_{GE} = 15V$

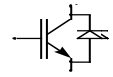
**vorläufige Daten**  
**preliminary data**



**Ausgangskennlinienfeld (typisch)**  
**Output characteristic (typical)**

$I_c = f(V_{CE})$   
 $T_{vj} = 125°C$

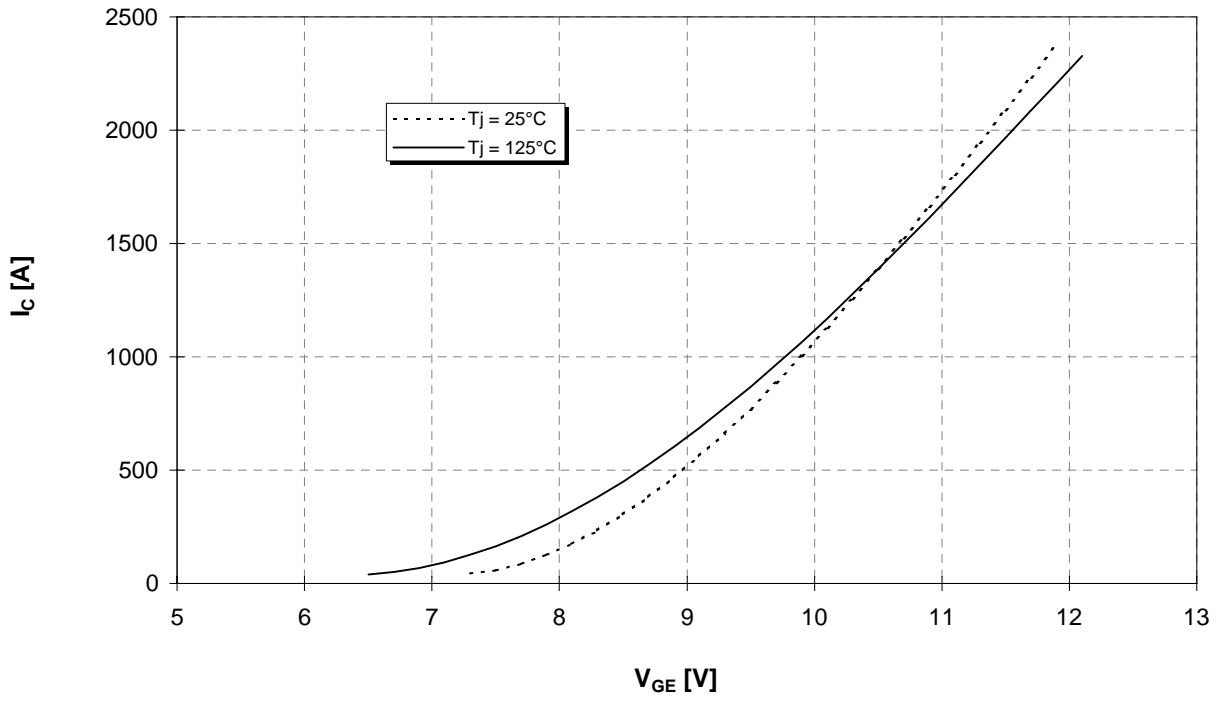




vorläufige Daten  
preliminary data

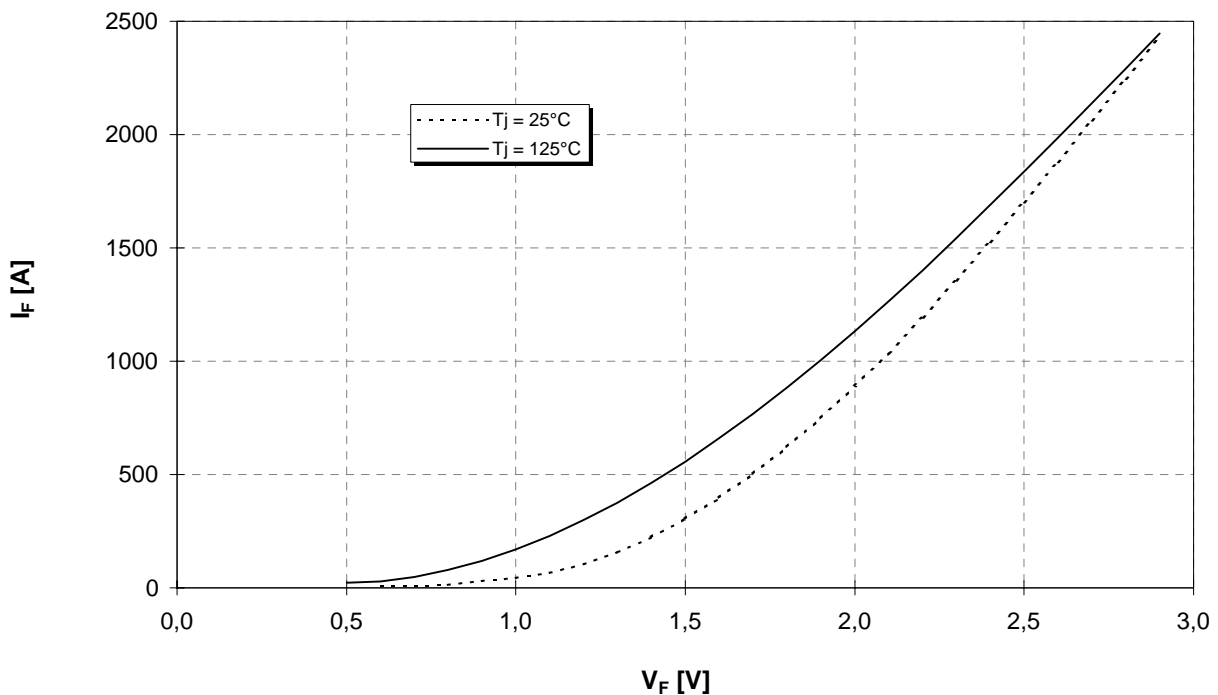
Übertragungscharakteristik (typisch)  
Transfer characteristic (typical)

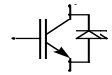
$I_c = f(V_{GE})$   
 $V_{CE} = 20V$



Durchlaßkennlinie der Inversdiode (typisch)  
Forward characteristic of inverse diode (typical)

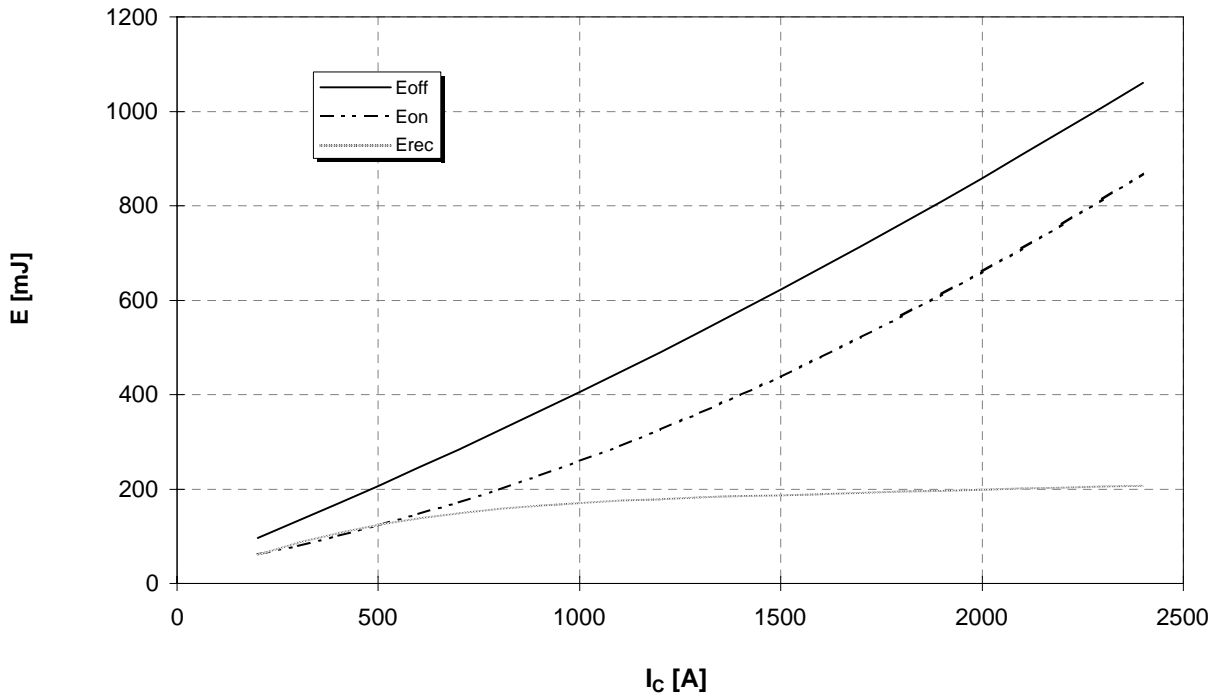
$I_F = f(V_F)$



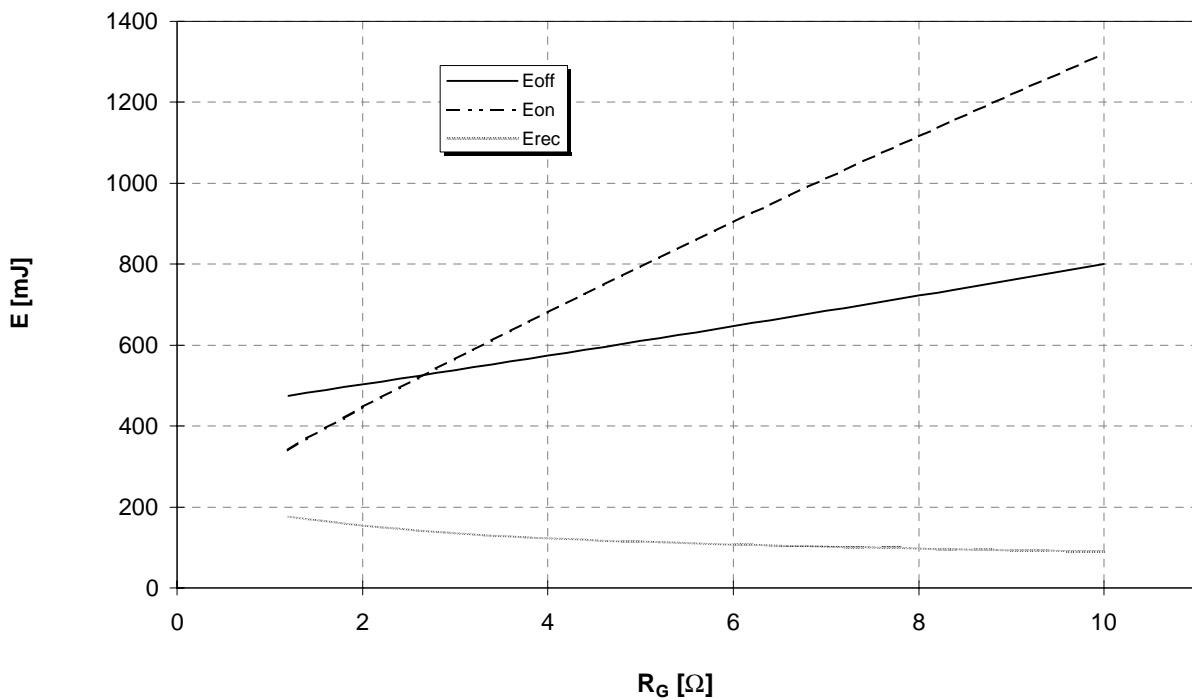


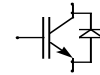
vorläufige Daten  
preliminary data

Schaltverluste (typisch)  $E_{on} = f(I_C), E_{off} = f(I_C), E_{rec} = f(I_C)$   
 Switching losses (typical)  $R_{gon} = R_{goff} = 1,2 \Omega, V_{CE} = 900V, T_j = 125^\circ C, V_{GE} = \pm 15V$



Schaltverluste (typisch)  $E_{on} = f(R_G), E_{off} = f(R_G), E_{rec} = f(R_G)$   
 Switching losses (typical)  $I_C = 1200A, V_{CE} = 900V, T_j = 125^\circ C, V_{GE} = \pm 15V$



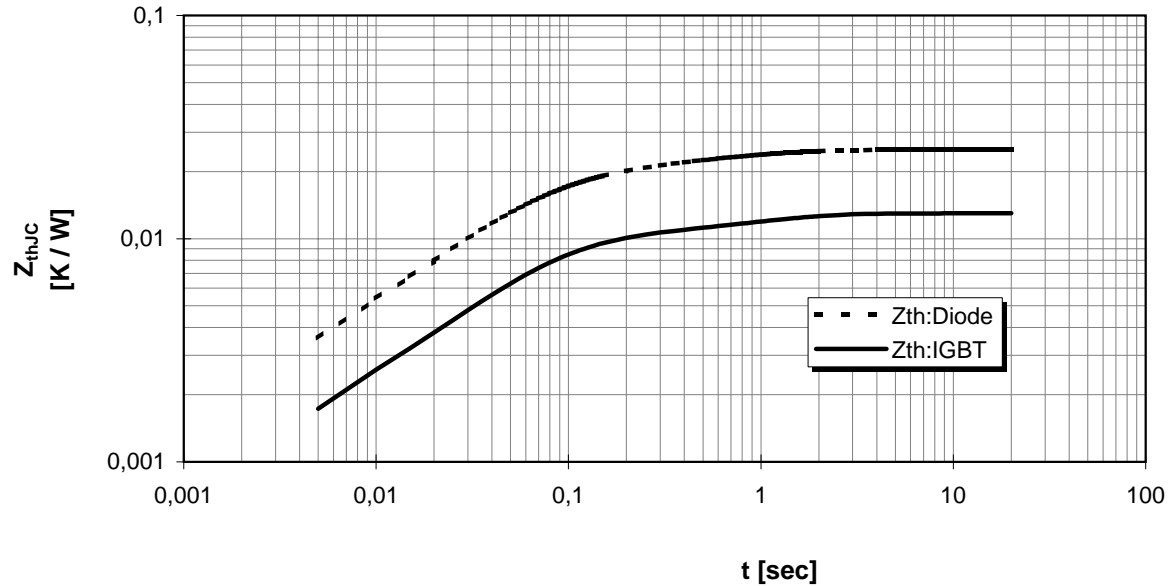


vorläufige Daten

preliminary data

Transienter Wärmewiderstand  
Transient thermal impedance

$$Z_{thJC} = f(t)$$

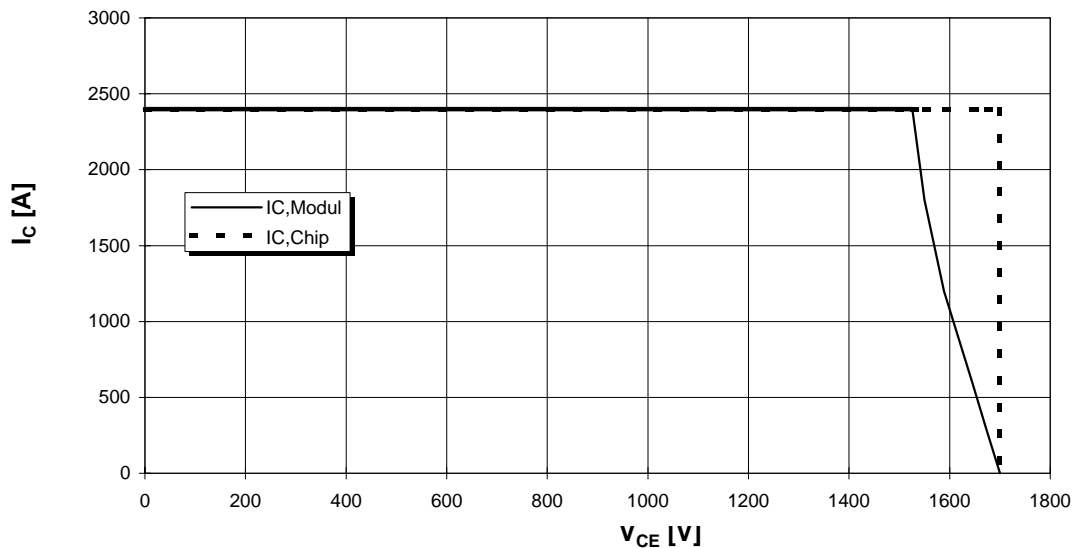


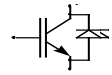
i	1	2	3	4
r <sub>i</sub> [K/kW] : IGBT	1,25	6,15	2,6	3
τ <sub>i</sub> [sec] : IGBT	0,003	0,05	0,1	0,95
r <sub>i</sub> [K/kW] : Diode	2,46	13,4	4,57	4,57
τ <sub>i</sub> [sec] : Diode	0,003	0,045	0,45	0,75

Sicherer Arbeitsbereich (RBSOA)

Reverse bias safe operation area (RBSOA)

R<sub>θ</sub> = 1,2 Ohm, T<sub>vj</sub> = 125°C





Äußere Abmessungen / external dimensions

